

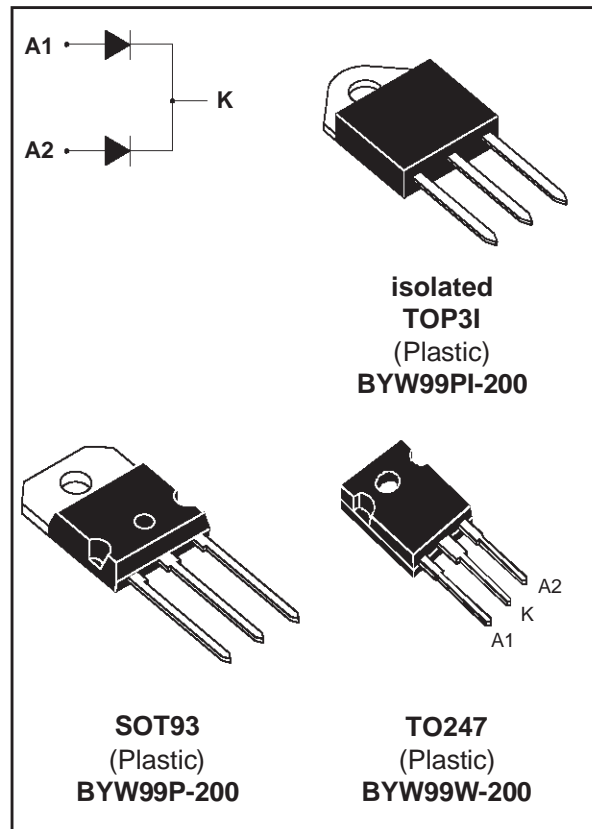
HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED VERSION TOP3I :
Insulating voltage = 2500 V DC
Capacitance = 12 pF

DESCRIPTION

Dual center tap rectifier suited for switchmode power supply and high frequency DC to DC converters.
Packaged in SOT93, TOP3I or TO247 this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit	
$I_{F(RMS)}$	RMS forward current			35	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	SOT93 / TO247	$T_c = 120^\circ\text{C}$	Per diode	15	A
		TOP3I	$T_c = 115^\circ\text{C}$	Per diode	15	A
I_{FSM}	Surge non repetitive forward current		$t_p = 10\text{ms}$ sinusoidal	Per diode	200	A
T_{stg} T_j	Storage and junction temperature range			- 40 to + 150 - 40 to + 150	$^\circ\text{C}$ $^\circ\text{C}$	

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	200	V

BYW99P/PI/W**THERMAL RESISTANCES**

Symbol	Parameter			Value	Unit
Rth (j-c)	Junction to case	SOT93 / TO247	Per diode	1.8	°C/W
			Total	1.0	
		TOP3I	Per diode	2.0	
			Total	1.25	
Rth (c)	Coupling	SOT93 / TO247		0.2	°C/W
		TOP3I		0.5	

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c (\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{RRM}			20	μA
	T _j = 100°C				1.5	mA
V _F **	T _j = 125°C	I _F = 12 A			0.85	V
	T _j = 125°C	I _F = 25 A			1.05	
	T _j = 25°C	I _F = 25 A			1.15	

Pulse test : * tp = 5 ms, δ < 2 %

** tp = 380 μs, δ < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.016 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A I _R = 1A			25	ns
		I _F = 1A V _R = 30V		dI _F /dt = -50A/μs	40	
tfr	T _j = 25°C	I _F = 1A V _{FR} = 1.1 x V _F		15		ns
V _{FP}	T _j = 25°C	I _F = 1A		2		V

Fig.1 : Average forward power dissipation versus average forward current.

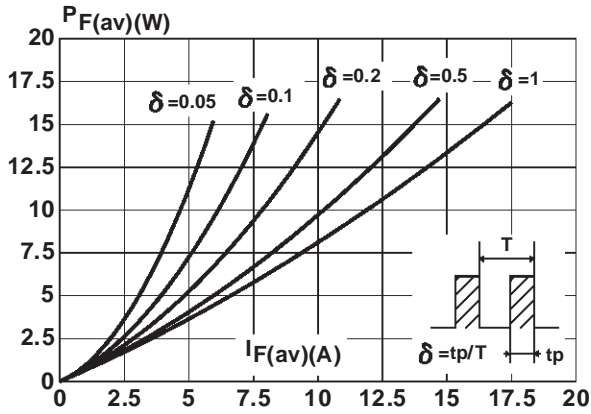


Fig.2 : Peak current versus form factor.

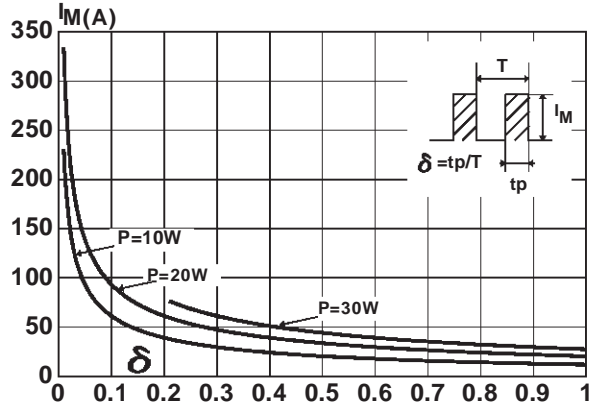


Fig.3 : Forward voltage drop versus forward current (maximum values).

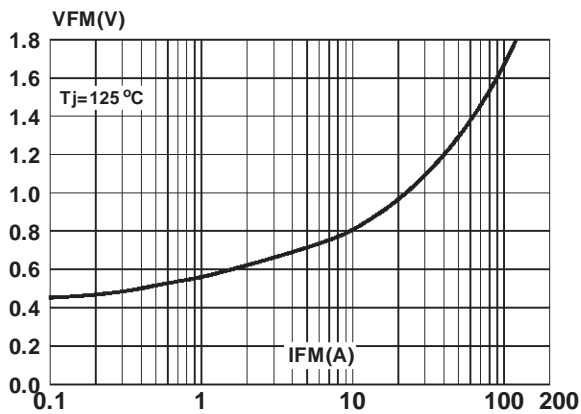


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

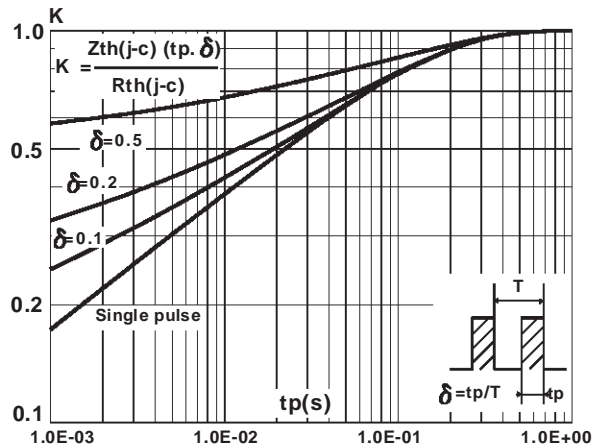


Fig.5 : Non repetitive surge peak forward current versus overload duration. (SOT93, TO247)

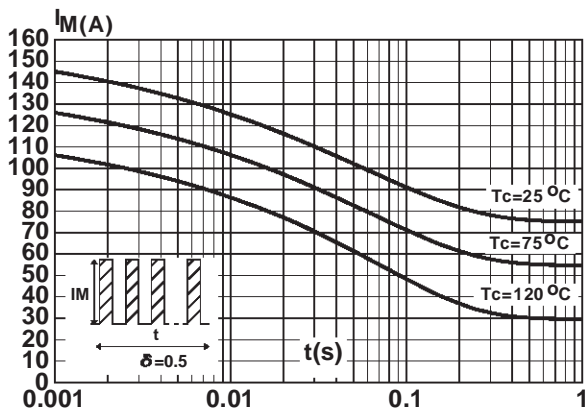


Fig.6 : Non repetitive surge peak forward current versus overload duration. (TOP31)

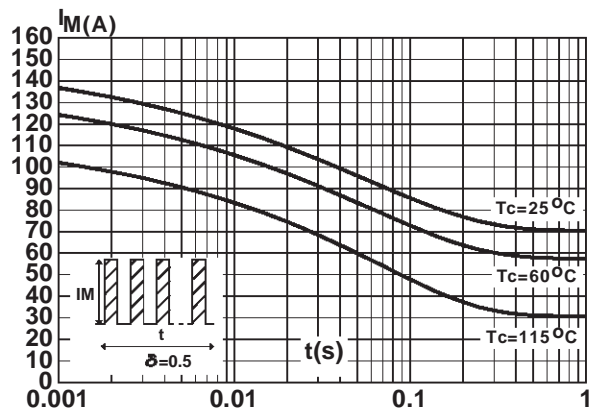


Fig.7 : Average current versus ambient temperature.
($\delta = 0.5$) (SOT93, TO247)

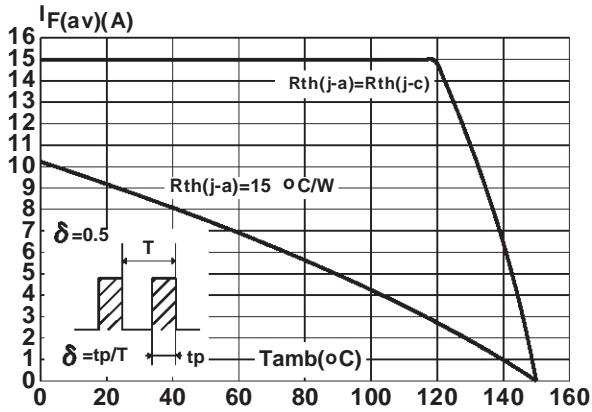


Fig.8 : Average current versus ambient temperature.
($\delta = 0.5$) (TOP3I)

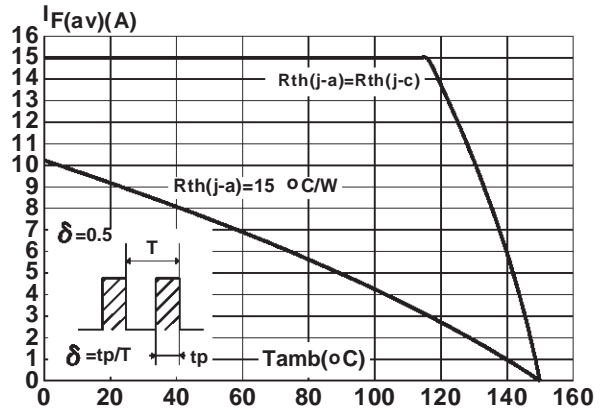


Fig.9 : Junction capacitance versus reverse voltage applied (Typical values).

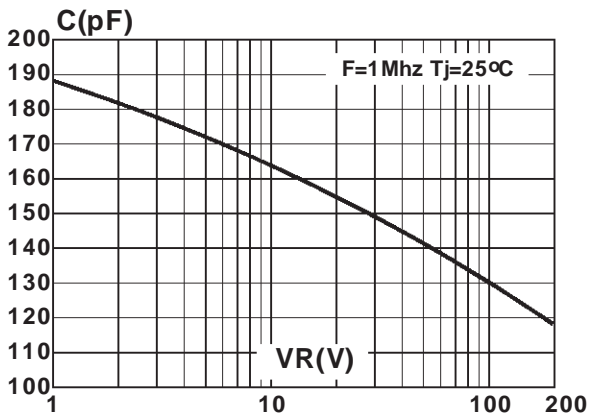


Fig.10 : Recovery charges versus dI_F/dt .

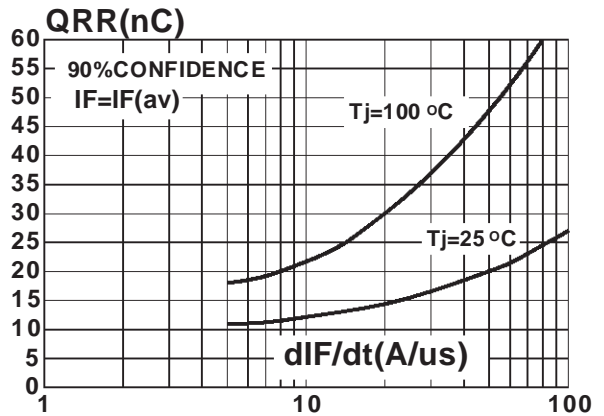


Fig.11 : Peak reverse current versus dI_F/dt .

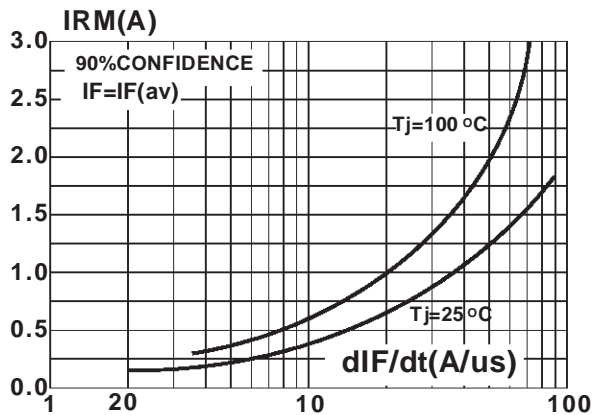
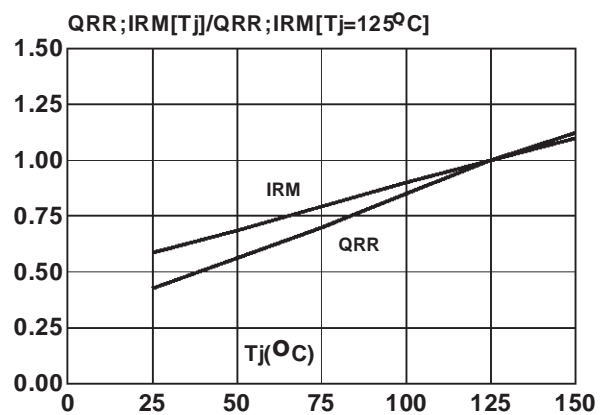
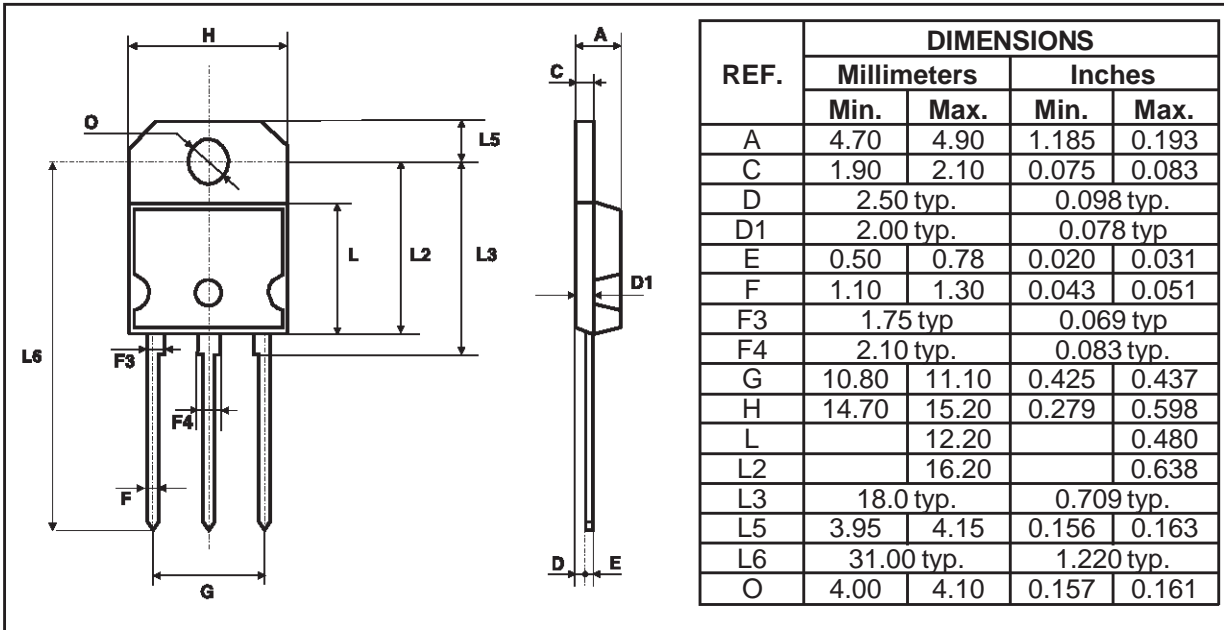


Fig.12 : Dynamic parameters versus junction temperature.

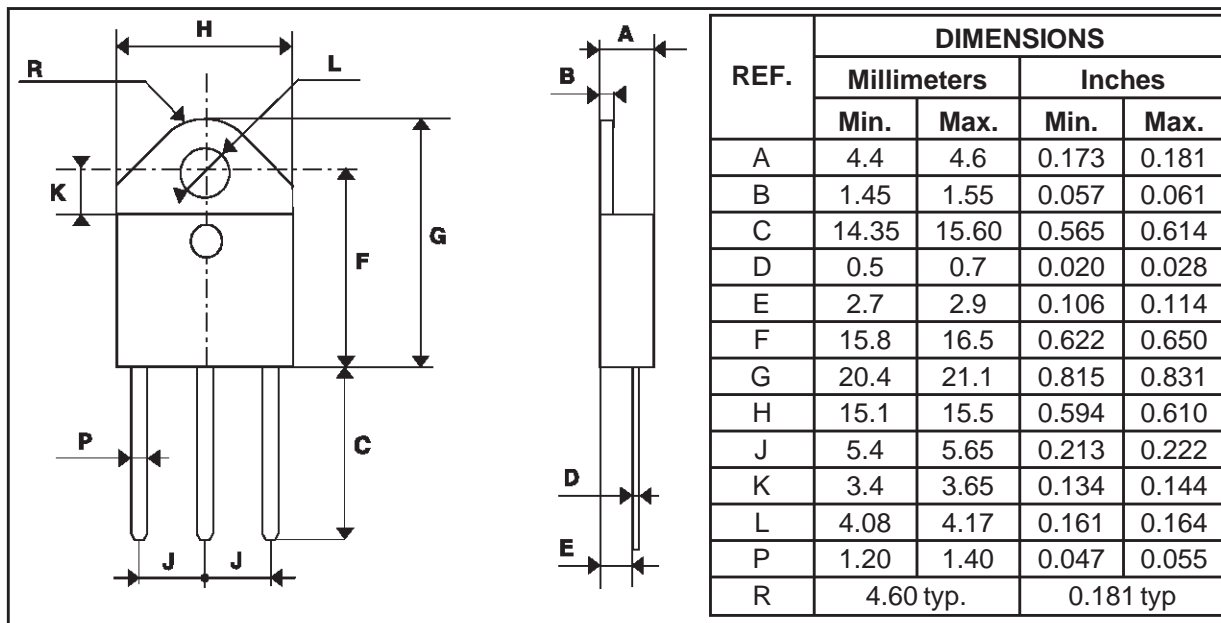


PACKAGE MECHANICAL DATA
SOT93



- **Marking** : Type number
- **Cooling method** : C
- **Weight** : 5.3 g
- **Recommended torque value** : 0.8m.N
- **Maximum torque value** : 1.0m.N

PACKAGE MECHANICAL DATA
TOP3I (isolated)

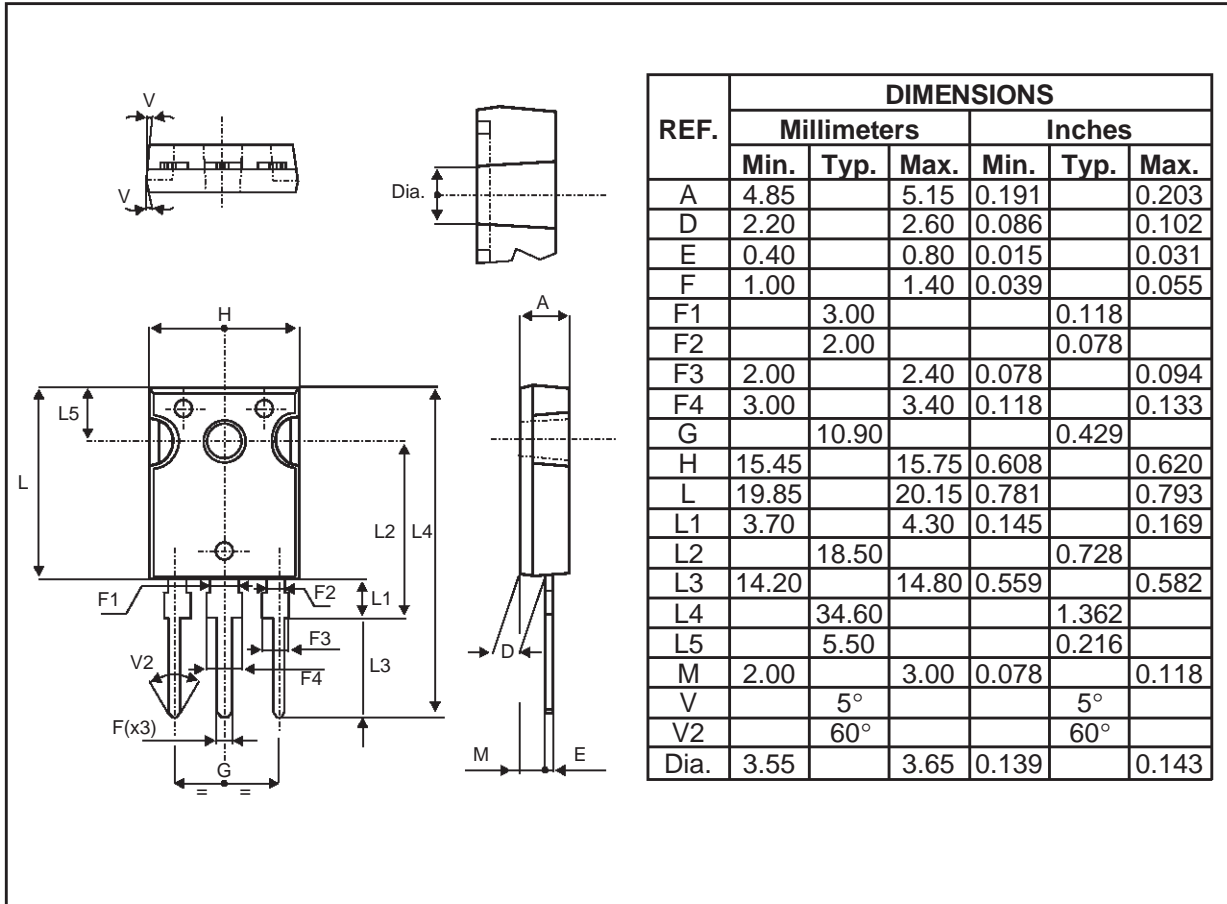


- **Marking** : Type number
- **Cooling method** : C
- **Weight** : 4.7 g
- **Recommended torque value** : 0.8m.N
- **Maximum torque value** : 1.0m.N



BYW99P/PI/W

PACKAGE MECHANICAL DATA TO247



- **Marking** : Type number
- **Cooling method** : C
- **Weight** : 4.4 g
- **Recommended torque value** : 0.8m.N
- **Maximum torque value** : 1.0m.N

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